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Atty Docket No 10191/2197	Serial No 10/030,309
	10/030.307
Applicant(s)	
Alfred GOERLACH	Group

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	PATENT DATE	NAME	CLASS	SUBCLASS	FILING DATE

## FOREIGN PATENT DOCUMENTS

EV. M. T.	DOCUMENT.					TRANSLATION	
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	YES	NO
PF	197 05 728	August 20, 1998	DE			_	
DF	08264811	October 11, 1996	JP				

## OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
PF	K. J. Schoen et al., "High Voltage GalnP/GaAs Dual Material Schottky Rectifiers," Appl. Phys. Lett. Vol. 71, No. 4, pp. 518 to 520, July 28, 1997
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EXAMINER Day Man-	DATE CONSIDERED	(1/23/0)
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw not considered, include copy of this form with next communication to applicant	line through citation if not	in conformance and